

# N-Channel MOSFET Transistor

## **2SK216 / K216**

200V / 0.5A

# DATASHEET

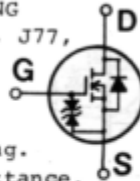
OEM – Hitachi

Source: Hitachi Databook Power Mosfet Data 4/83

# 2SK213, 2SK214, 2SK215, 2SK216

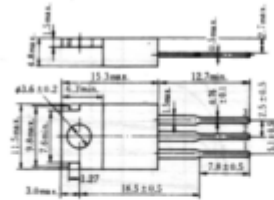
## SILICON N-CHANNEL MOS FET

HIGH FREQUENCY AND LOW FREQUENCY POWER AMPLIFIER, HIGH SPEED SWITCHING  
Complementary Pair with 2SJ76, J77, J78, J79



**Features;**

- Suitable for Direct Mounting.
- High Forward Transfer Admittance.
- Excellent Frequency Response.
- Enhancement-Mode.



(Dimensions in mm)  
(JEDEC TO-220AB)

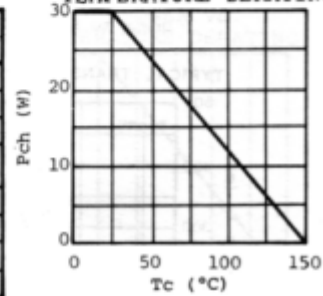
1. Gate
2. Source (Flange)
3. Drain

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	Ratings				Unit
		K213	K214	K215	K216	
Drain-Source Voltage	V <sub>DSX</sub>	140	160	180	200	V
Gate-Source Voltage	V <sub>GSS</sub>	±15				V
Drain Current	I <sub>D</sub>	500				mA
Body-Drain Diode Reverse Drain Current	I <sub>DR</sub>	500				mA
Channel Dissipation	P <sub>ch</sub>	1.75				W
	P <sub>ch</sub> *	30				W
Channel Temperature	T <sub>ch</sub>	150				°C
Storage Temperature	T <sub>stg</sub>	-45 ~ +150				°C

\*Value at Tc=25°C

POWER VS. TEMPERATURE DERATING



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Drain-Source Breakdown Voltage	K213	I <sub>D</sub> =1mA, V <sub>GS</sub> =-2V	140	-	-	V
	K214		160	-	-	V
	K215		180	-	-	V
	K216		200	-	-	V
Gate-Source Breakdown Voltage	V <sub>(BR)GSS</sub>	I <sub>G</sub> =±10μA, V <sub>DS</sub> =0	±15	-	-	V
Gate-Source Voltage	V <sub>GS(on)</sub>	I <sub>D</sub> =10mA, V <sub>DS</sub> =10V*	0.2	-	1.5	V
Drain-Source Saturation Voltage	V <sub>DS(sat)</sub>	I <sub>D</sub> =10mA, V <sub>GD</sub> =0 *	-	-	2.0	V
Forward Transfer Admittance	y <sub>fs</sub>	I <sub>D</sub> =10mA, V <sub>DS</sub> =20V*	-	40	-	mS
Input Capacitance	C <sub>iss</sub>	I <sub>D</sub> =10mA, V <sub>DS</sub> =10V, f=1MHz	-	90	-	pF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	2.2	-	pF

2SK213,2SK214,2SK215,2SK216

